

MURF1620CTG

Switch-mode Power Rectifier

These state-of-the-art devices are designed for use in switching power supplies, inverters and as free wheeling diodes.

Features

- Ultrafast 35 Nanosecond Recovery Times
- 150°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- High Temperature Glass Passivated Junction
- Low Leakage Specified @ 150°C Case Temperature
- Current Derating @ Both Case and Ambient Temperatures
- Electrically Isolated. No Isolation Hardware Required.
- ESD Rating:
 - ◆ Human Body Model = 3B (> 8 kV)
 - ◆ Machine Model = C (> 400 V)
- This is a Pb-Free Package*

Mechanical Characteristics:

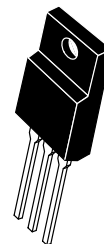
- Case: Epoxy, Molded
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



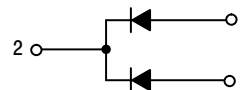
ON Semiconductor®

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**ULTRAFAST RECTIFIER
16 AMPERES, 200 VOLTS**



**ISOLATED TO-220
CASE 221AH**



MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
U1620 = Device Code
G = Pb-Free Package
AKA = Diode Polarity

ORDERING INFORMATION

Device	Package	Shipping†
MURF1620CTG	TO-220 (Pb-Free)	50 Units / Rail

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MURF1620CTG

MAXIMUM RATINGS (Per Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	200	V
Average Rectified Forward Current Per Diode, (Rated V_R), $T_C = 150^\circ\text{C}$ Total Device	$I_{F(AV)}$	8 16	A
Peak Repetitive Forward Current (Rated V_R , Square Wave, 20 kHz), $T_C = 150^\circ\text{C}$	I_{FM}	16	A
Non-repetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	100	A
Operating Junction and Storage Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
RMS Isolation Voltage ($t = 0.3$ second, R.H. $\leq 30\%$, $T_A = 25^\circ\text{C}$) (Note 1)	V_{iso1}	4500	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Proper strike and creepage distance must be provided.

THERMAL CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	4.2	$^\circ\text{C/W}$
Lead Temperature for Soldering Purposes: 1/8" from the Case for 5 seconds	T_L	260	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) ($i_F = 8.0$ A, $T_C = 150^\circ\text{C}$) ($i_F = 8.0$ A, $T_C = 25^\circ\text{C}$)	V_F	0.895 0.975	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, $T_C = 150^\circ\text{C}$) (Rated DC Voltage, $T_C = 25^\circ\text{C}$)	i_R	250 5.0	μA
Maximum Reverse Recovery Time ($I_F = 1.0$ A, $di/dt = 50$ A/ μs) ($I_F = 0.5$ A, $i_R = 1.0$ A, $I_{REC} = 0.25$ A)	t_{rr}	35 25	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

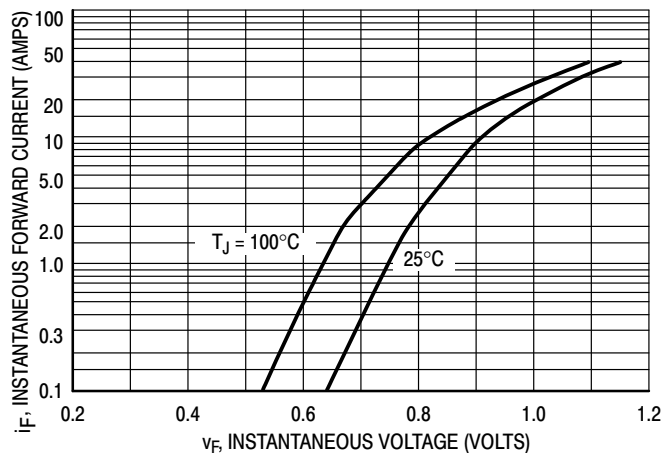


Figure 1. Typical Forward Voltage, Per Leg

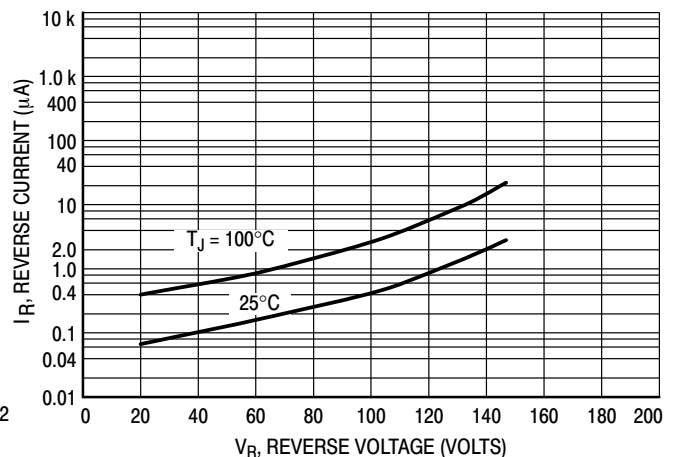
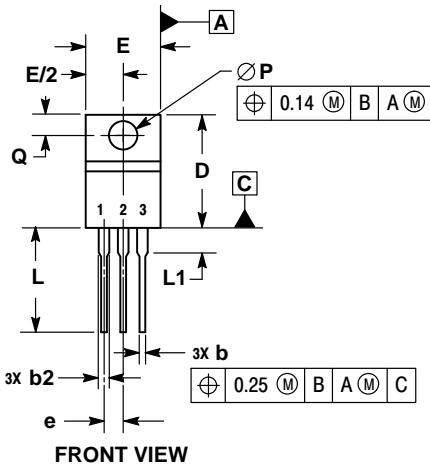


Figure 2. Typical Reverse Current, Per Leg*

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PACKAGE DIMENSIONS

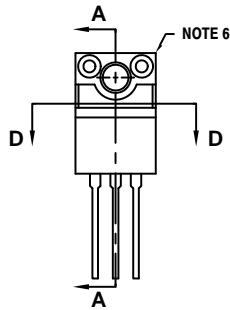
TO-220 FULLPACK, 3-LEAD CASE 221AH ISSUE F



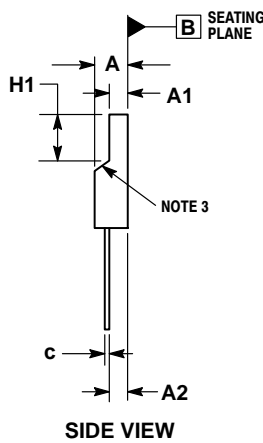
FRONT VIEW



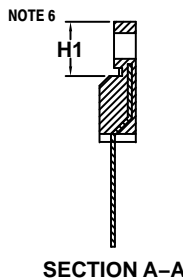
SECTION D-D



ALTERNATE CONSTRUCTION



SIDE VIEW




SECTION A-A

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR UNCONTROLLED IN THIS AREA.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
6. CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOPE DEFINED BY DIMENSIONS A1 AND H1 FOR MANUFACTURING PURPOSES.

DIM	MILLIMETERS	
	MIN	MAX
A	4.30	4.70
A1	2.50	2.90
A2	2.50	2.90
b	0.54	0.84
b2	1.10	1.40
c	0.49	0.79
D	14.70	15.30
E	9.70	10.30
e	2.54 BSC	
H1	6.60	7.10
L	12.50	14.73
L1	---	2.80
P	3.00	3.40
Q	2.80	3.20

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